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(71) Applicant *(for all designated States except US)*: **S.O.I.TEC SILICON ON INSULATOR TECHNOLOGIES S.A.** [FR/FR]; Parc Technologique des Fontaines, Bernin, F-38926 Crolles Cedex (FR).

(72) Inventors; and
(75) Inventors/Applicants *(for US only)*: **LETERTRE, Fabrice** [FR/FR]; 33 quai Jongkind, F-38000 Grenoble (FR). **FAURE, Bruce** [FR/FR]; 4, Place de la Claveyson, F-38000 Grenoble (FR).

(74) Agent: **BERTRAM, Rainer**; Grünecker, Kinkeldey, Stockmair & Schwanhäusser, Maximilianstrasse 58, 80538 München (DE).

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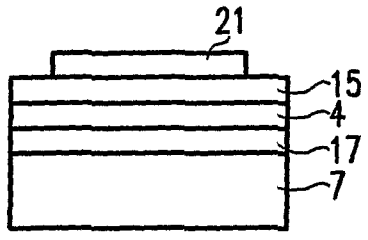
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(54) Title: METHOD OF PRODUCING A SUBSTRATE FOR AN OPTOELECTRONIC APPLICATION



(57) Abstract: The present invention relates to a method of producing a substrate for an optoelectronic application, the substrate having at least one active nitride layer on a final carrier and a metallic intermediate layer therebetween, wherein the method comprises: preparation of an auxiliary substrate wherein one semi-conducting nitride layer is placed on an auxiliary carrier; metallising the auxiliary substrate on the side of the nitride layer; bonding of the metallised carrier substrate with the final carrier; and removing of the auxiliary carrier after the bonding step. It is the object of the present invention to provide a method of this type in which the crystalline quality of the active nitride layer(s) can be improved. The object is solved by a method of the above mentioned type wherein the step of preparing the auxiliary substrate comprises: detaching a part from a massive semi-conducting nitride substrate; and transferring said part onto the auxiliary carrier to form the semi-conducting nitride layer thereon.